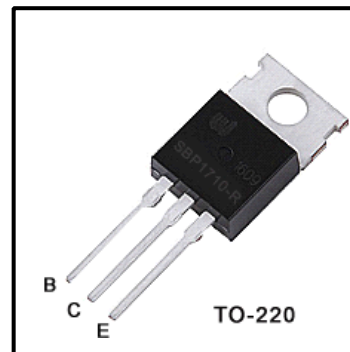


*High Voltage Fast-Switching NPN Power Transistor*
**Features**

- Very high switching speed
- High Voltage Capability
- Wide Reverse Bias SOA

**General Description**

This Device is designed for high voltage, High speed switching characteristics required such as lighting system, switching mode power supply.


**Absolute Maximum Ratings**

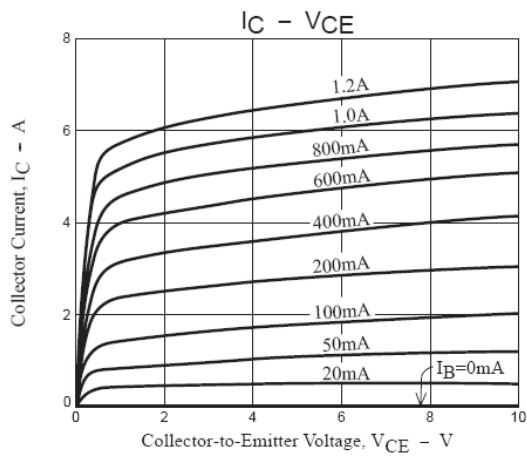
Symbol	Parameter	Test Conditions	Value	Units
$V_{CBO}$	Collect-Emmitter Voltage	$V_{BE}=0$	900	V
$V_{CEO}$	Collector-Emmitter Voltage	$I_B=0$	500	V
$V_{EBO}$	Emmitter-Base Voltage	$I_C=0$	7	V
$I_C$	Collector Current		7	A
$I_{CP}$	Collector pulse Current (Note)		14	A
$P_C$	Total Dissipation at $T_c=25^\circ\text{C}$		45	W
$T_J$	Operation Junction Temperature		150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature		-55~150	$^\circ\text{C}$

## Electrical Characteristics (T<sub>c</sub>=25°C unless otherwise noted)

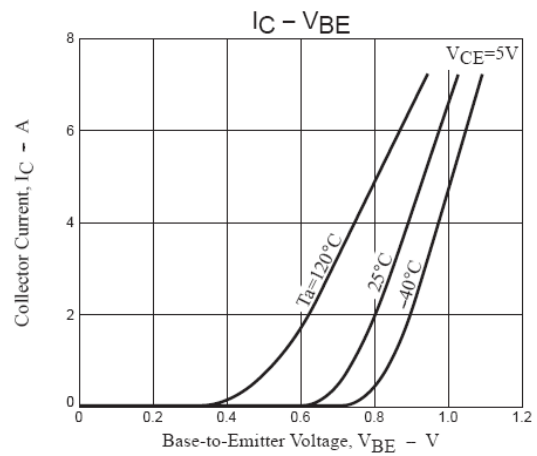
Symbol	Parameter	Test conditions	Value			Units
			Min	Typ	Max	
I <sub>CBO</sub>	Collector Cut-off Current	V <sub>CB</sub> =500V, I <sub>e</sub> =0A	-	-	10	μA
I <sub>EBO</sub>	Emitter Cut-off Current	V <sub>EB</sub> =5V, I <sub>c</sub> =0A	-	-	10	μA
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>c</sub> =1mA, I <sub>e</sub> =0	900	-	-	V
BV <sub>CEO</sub>	Collector-Emmitter Breakdown Voltage	I <sub>c</sub> =5mA, I <sub>b</sub> =open	500	-	-	V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>e</sub> =1mA, I <sub>c</sub> =0	7	-	-	V
V <sub>CE(sat)</sub>	Collector -Emmitter Saturation Voltage	I <sub>c</sub> =3A, I <sub>b</sub> =0.6A	-	-	1	V
V <sub>BE(sat)</sub>	Base -Emmitter saturation Voltage	I <sub>c</sub> =3A, I <sub>b</sub> =0.6A	-	-	1.5	V
I <sub>EBO</sub>	Emitter -Base Cutoff Current	V <sub>eb</sub> =5V, I <sub>c</sub> =0	-	-	10	μA
hFE	DC Current Gain	V <sub>ce</sub> =5V, I <sub>c</sub> =0.6A	20	-	50	
		V <sub>ce</sub> =5V, I <sub>c</sub> =3A	8	-	-	
f <sub>T</sub>	Gain-Bandwidth Product	V <sub>ce</sub> =10V, I <sub>c</sub> =0.6A	-	-	18	MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, f=1MHz	-	-	80	pF
t <sub>on</sub>	Turn on Time	V <sub>CC</sub> =5V, I <sub>c</sub> =0.5A	-	-	0.6	μs
t <sub>s</sub>	Storage Time	V <sub>CC</sub> =5V, I <sub>c</sub> =0.5A	3	-	8	μs
t <sub>r</sub>	Fall Time	V <sub>CC</sub> =5V, I <sub>c</sub> =0.5A	-	-	0.4	μs

Note:

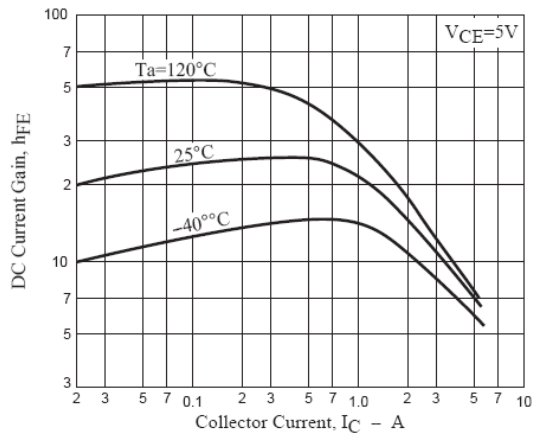
Pulse Test: Pulse width ≤ 300μs; Duty cycle 10%



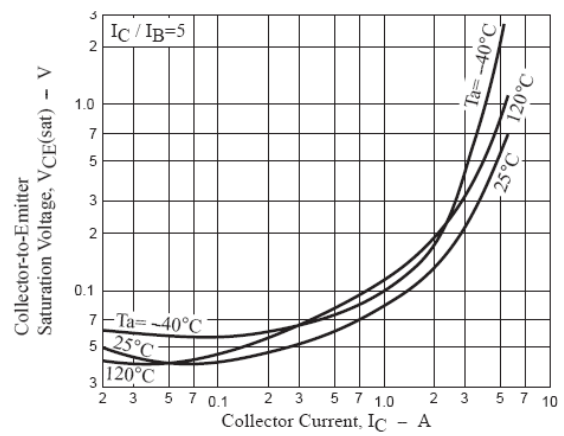
**Fig. 1 Collector Current VS Collector-Emitter Voltage**



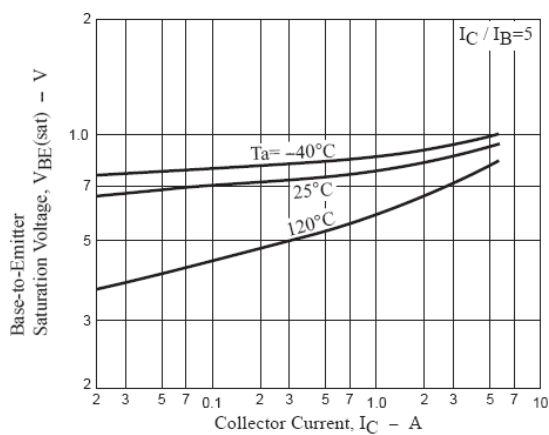
**Fig. 2 Collector Current VS Emitter-Base Voltage**



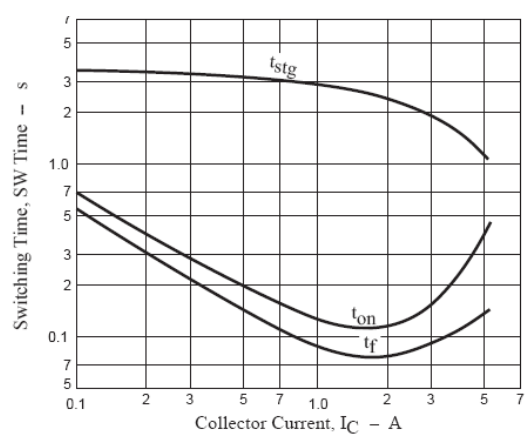
**Fig. 3 DC Current Gain**



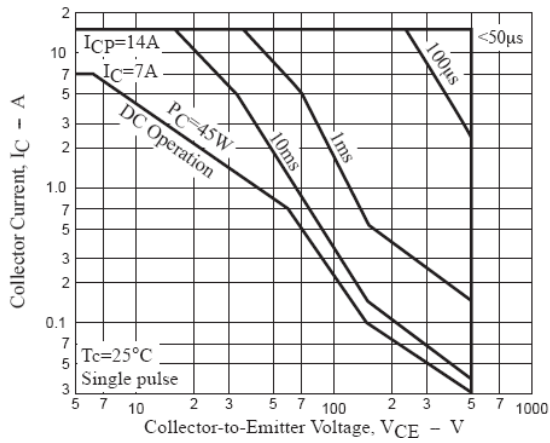
**Fig. 4 Collector-Emitter Saturation Voltage**



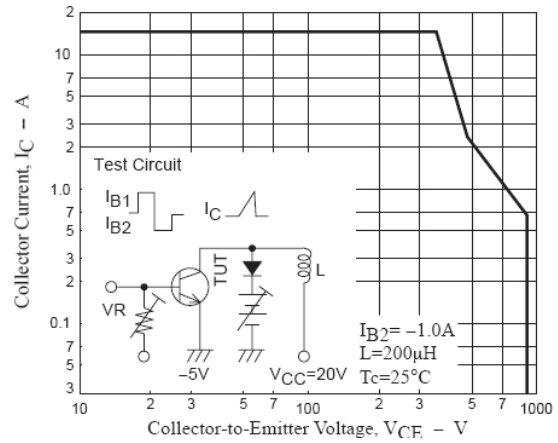
**Fig. 5 Base-Emitter Saturation Voltage**



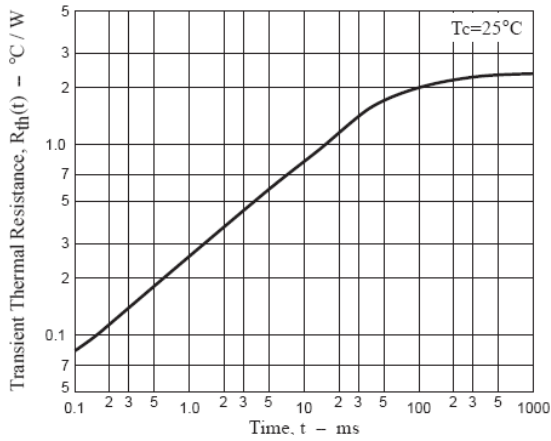
**Fig.6 Switching Time**



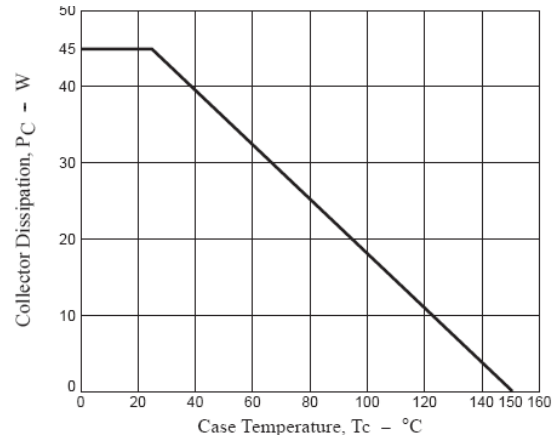
**Fig.7 Safe Operation Area**



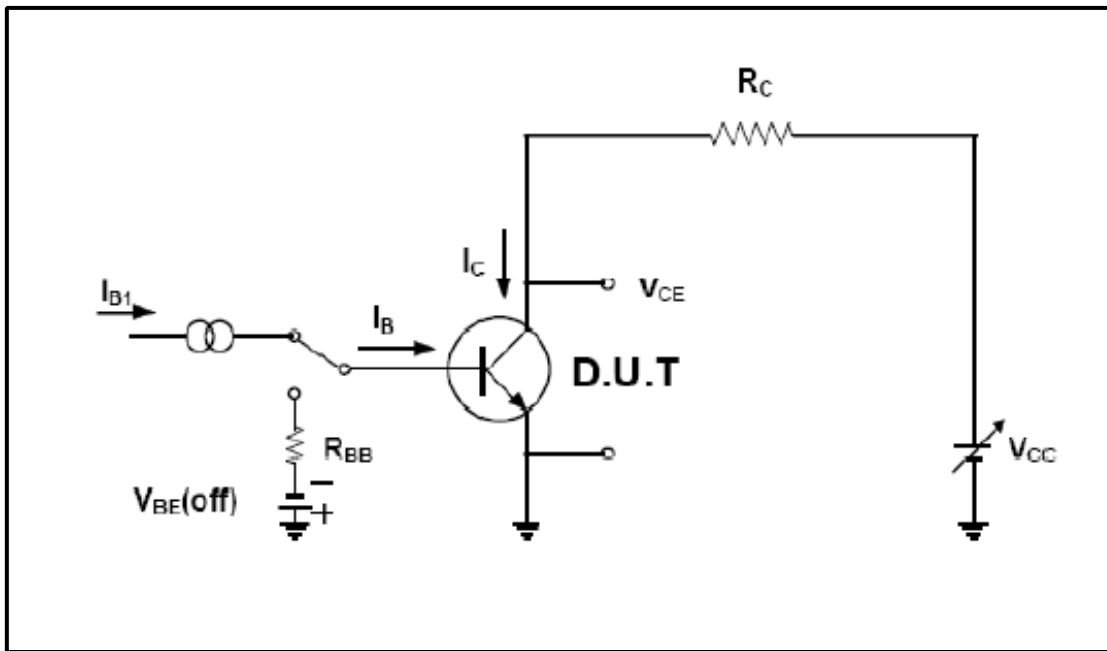
**Fig.8 Reverse Biased Safe Operation Area**



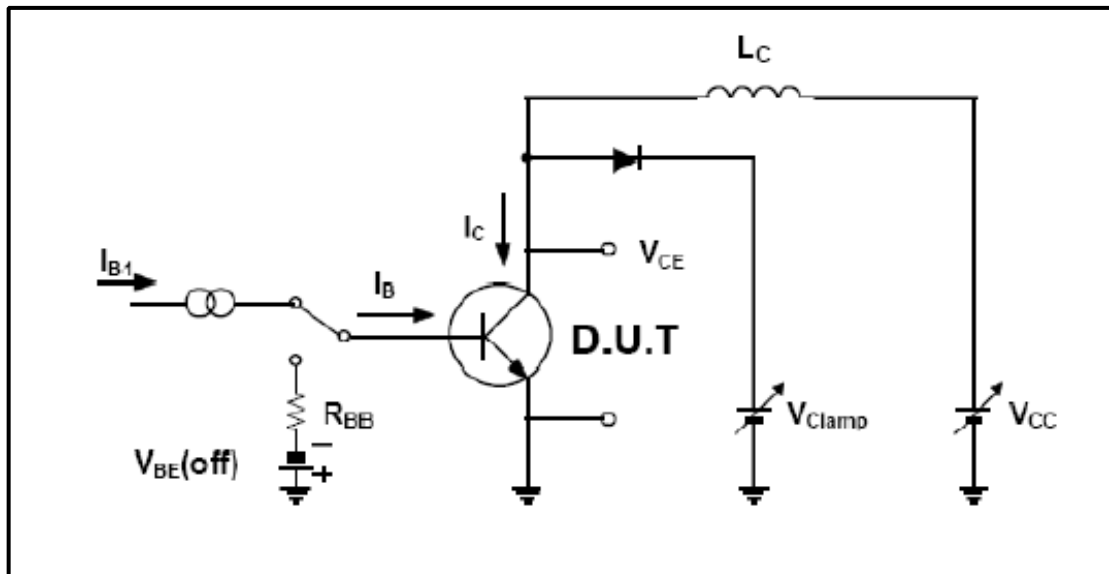
**Fig.9 Thermal Resistance**



**Fig.10 Power Derating**



**Fig.11 Inductive Load Switching & RBSOA Test Circuit**



**Fig.12 Inductive Load Switching & RBSOA Test Circuit**

**To-220 Package Dimension**

